Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

Features

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 V
- On-State Current Rating of 0.8 A RMS at 80°C
- High Surge Current Capability 10 A
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dV/dt 20 V/µsec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity
- Pb-Free Packages are Available*

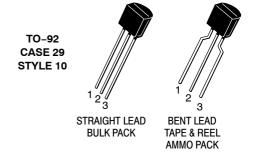


ON Semiconductor®

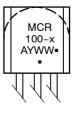
http://onsemi.com

SCRs 0.8 A RMS 100 thru 600 V

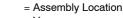




MARKING DIAGRAM



= Specific Device Code х А



Y = Year ww

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT				
1 Cathode				
2	Gate			
3	Anode			

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Notes 1 and 2) ($T_J = -40$ to 110°C, Sine Wave, 50 to 60 Hz; $R_{GK} = 1 \text{ k}\Omega$) MCR100–3 MCR100–4 MCR100–6 MCR100–8	V _{DRM,} V _{RRM}	100 200 400 600	V
On-State RMS Current, (T _C = 80°C) 180° Conduction Angles	I _{T(RMS)}	0.8	А
Peak Non-Repetitive Surge Current, (1/2 Cycle, Sine Wave, 60 Hz, T_{J} = 25°C)	I _{TSM}	10	А
Circuit Fusing Consideration, (t = 8.3 ms)	l ² t	0.415	A ² s
Forward Peak Gate Power, (T_A = 25°C, Pulse Width \leq 1.0 µs)	P _{GM}	0.1	W
Forward Average Gate Power, (T _A = 25° C, t = 8.3 ms)	P _{G(AV)}	0.01	W
Forward Peak Gate Current, (T _A = 25°C, Pulse Width $\leq 1.0 \mu$ s)	I _{GM}	1.0	А
Reverse Peak Gate Voltage, (T _A = 25°C, Pulse Width \leq 1.0 µs)	V _{GRM}	5.0	V
Operating Junction Temperature Range @ Rate V_{RRM} and V_{DRM}	TJ	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
See ordering information for exact device number options.

THERMAL CHARACTERISTICS

Characteristic		Symi	loc	Max		Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient		R _{θJ} R _{θJ}		75 200	0	C/W
Lead Solder Temperature (<1/16" from case, 10 secs max)		ΤL		260		°C
ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)					•	
Characteristic	Sym	bol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current (Note 3) $T_{C} = 25^{\circ}C$	I _{DRM} ,	I _{RRM}	_	_	10	μA
$(V_D = Rated V_{DRM} and V_{RRM}; R_{GK} = 1 k\Omega)$ $T_C = 110^{\circ}C$			-	-	100	
ON CHARACTERISTICS			•	-	•	
Peak Forward On–State Voltage [*] (I _{TM} = 1.0 A Peak @ T _A = 25°C)	VT	M	-	-	1.7	V
$ \begin{array}{ll} \mbox{Gate Trigger Current (Note 4)} & T_{C} = 25^{\circ} C \\ \mbox{(V_{AK} = 7.0 Vdc, R_{L} = 100 } \Omega) \end{array} $	۱ _G	īT	-	40	200	μΑ
Holding Current (Note 3) $T_C = 25^{\circ}C$ (V _{AK} = 7.0 Vdc, Initiating Current = 20 mA, R _{GK} = 1 kΩ) $T_C = -40^{\circ}C$	۱	1		0.5	5.0 10	mA

DYNAMIC CHARACTERISTIC	S						
Gate Trigger Voltage (Note 4) (V _{AK} = 7.0 Vdc, R _L = 100 Ω)	$T_{C} = 25^{\circ}C$ $T_{C} = -40^{\circ}C$		V _{GT}		0.62 _	0.8 1.2	V
Latch Current (Note 4) (V _{AK} = 7.0 V, Ig = 200 μA)		$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	١L		0.6 _	10 15	mA
(VAK = 7.0 Vac, Initiating Curre	$mt = 20 \text{ mA}, \text{ R}_{\text{GK}} = 1 \text{ k}\Omega$	$1_{\rm C} = -40^{\circ}{\rm C}$		-	_	10	

Critical Rate of Rise of Off–State Voltage (V_D = Rated V _{DRM} , Exponential Waveform, R _{GK} = 1 k Ω ,T _J = 110°C)	dV/dt	20	35	-	V/µs	
Critical Rate of Rise of On-State Current (I _{PK} = 20 A; Pw = 10 μsec; diG/dt = 1 A/μsec, Igt = 20 mA)	di/dt	-	-	50	A/μs	

*Indicates Pulse Test: Pulse Width \leq 1.0 ms, Duty Cycle \leq 1%.

3. R_{GK} = 1000 Ω included in measurement.

4. Does not include R_{GK} in measurement.

Voltage Current Characteristic of SCR

+ Current

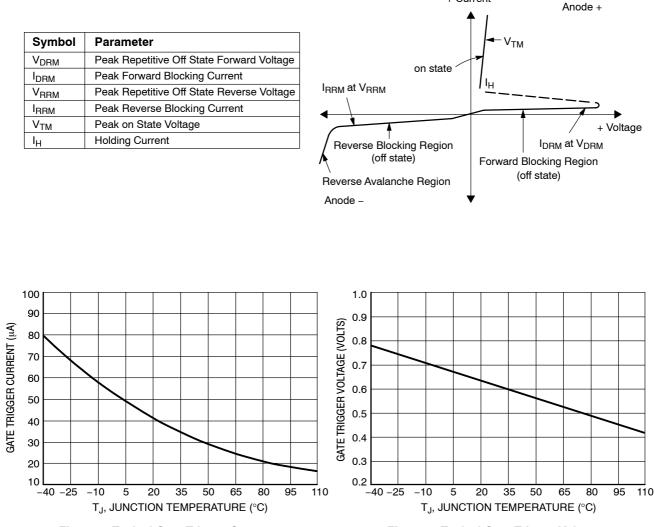
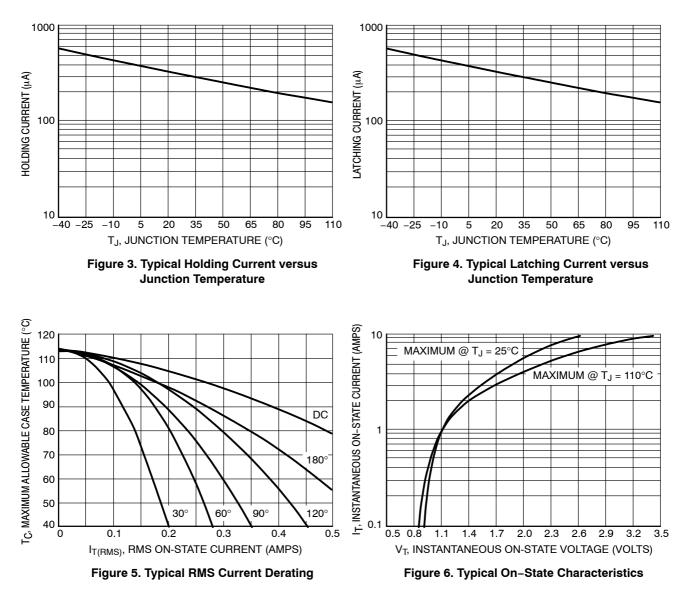


Figure 1. Typical Gate Trigger Current versus Junction Temperature

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature



ORDERING INFORMATION

Device	Package Code	Shipping [†]				
MCR100-003						
MCR100-004		5000 Units / Box				
MCR100-006						
MCR100-008						
MCR100-3RL						
MCR100-6RL	TO-92 (TO-226)	2000 / Tape & Reel				
MCR100-6RLRA						
MCR100-6RLRM		2222 / Terre & Arrive Deck				
MCR100-6ZL1		2000 / Tape & Ammo Pack				
MCR100-8RL		2000 / Tape & Reel				
MCR100-3G						
MCR100-4G		5000 Haita / Dave				
MCR100-6G		5000 Units / Box				
MCR100-8G						
MCR100-3RLG						
MCR100-6RLG	TO-92 (TO-226) (Pb-Free)	2000 / Tape & Reel				
MCR100-6RLRAG	(********)					
MCR100-4RLRMG						
MCR100-6RLRMG		2000 / Tape & Ammo Pack				
MCR100-6ZL1G						
MCR100-8RLG		2000 / Tape & Reel				

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TO-92 EIA RADIAL TAPE IN BOX OR ON REEL

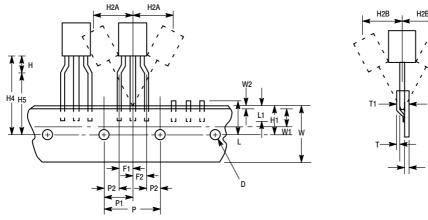


Figure 7. Device Positioning on Tape

		Specification			
		Inc	hes	Millin	neter
Symbol	Item	Min	Мах	Min	Max
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0
H1	Feedhole Location	0.3346	0.3741	8.5	9.5
H2A	Deflection Left or Right	0	0.039	0	1.0
H2B	Deflection Front or Rear	0	0.051	0	1.0
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11
L1	Lead Wire Enclosure	0.09842		2.5	
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20
T1	Overall Taped Package Thickness	_	0.0567	_	1.44
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65
W	Carrier Strip Width	0.6889	0.7481	17.5	19
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5

NOTES:

1. Maximum alignment deviation between leads not to be greater than 0.2 mm.

2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.

3. Component lead to tape adhesion must meet the pull test requirements.

4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.

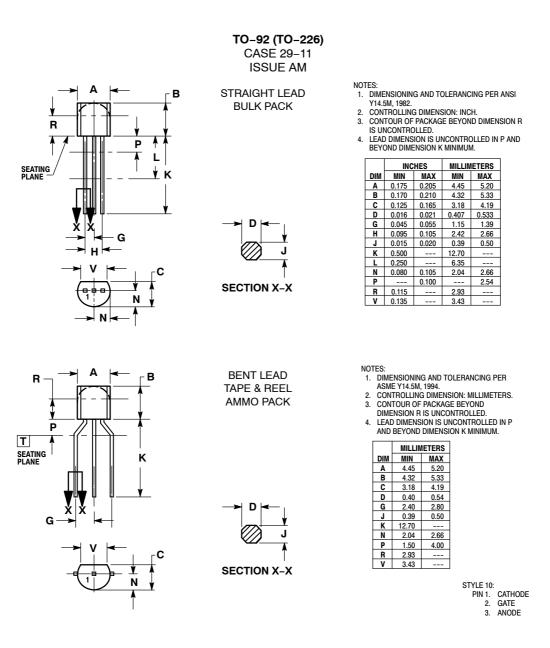
5. Hold down tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.

6. No more than 1 consecutive missing component is permitted.

7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.

8. Splices will not interfere with the sprocket feed holes.

PACKAGE DIMENSIONS



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